

ASC100N1200MEP4B

1200V, 100A, 16mΩ, Four-pack(H-Bridge), Silicon Carbide MOSFET Module

Product Data Sheet

ASTC-3T03-62A A/0



General Description

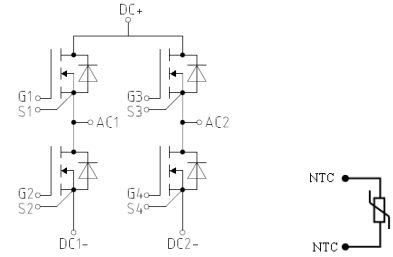
The AST-MEP module incorporates AST's 1200V Gen3 N-channel SiC MOSFET and solder pin type. NTC temperature sensor inside.

Features

- High Current Density
- Low Inductive Design
- Low Switching Losses
- High-frequency Operation
- Zero Turn-off Tail Current from MOSFET
- Normally-off, Fail-safe Device Operation
- Si₃N₄ Internal Isolation

Applications

- High Frequency Switching Application
- DC/DC Converter
- EV Chargers
- Welding



Ordering Informations

Order Number / Marking	ASC100N1200MEP4B
Package Type	MEP

Key Parameters

Symbol	Parameter	Values			Unit	Test Conditions
Absolute maximum rating						
V _{DS}	Drain-source Voltage	1200			V	T _C =25°C
I _D	Drain Current (continuous)	100			A	T _C =25°C
T _J	Junction Temperature	150			°C	
Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
Static characteristics						
R _{DS(on)}	Static Drain-source on Resistance	-	16	22	mΩ	V _{GS} =18V; I _D =50A; T _{VJ} =25°C
Dynamic characteristics						
Q _G	Total Gate Charge	-	239	-	nC	V _{DD} =800V; V _{GS} =-5/+18V; I _D =50A; T _C =25°C
Q _{GD}	Gate-drain Charge	-	78.5	-		
Source-drain diode						
Q _{RR}	Reverse Recovery Charge	-	615	-	nC	V _{GS} =-5/+18V; I _F =50A; V _R =800V; T _I =25°C

Absolute Maximum Ratings (at $T_c=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Values	Unit
V_{DS}	Drain-source Voltage	1200	V
V_{GS}	Gate-source Voltage	-10/+22	V
I_D	Drain Current (continuous)	100	A
I_{DM}	Drain Current (pulsed)	200	A
V_{isol}	Isolation Test Voltage (f=50Hz; t=1min)	3.0	kV
L_{Stray}	Stray Inductance	10	nH
T_J, T_{stg}	Junction and Storage Temperature Range	-40 to +150	$^{\circ}\text{C}$
M_S	Mounting Force Per Clamp	40 - 80	N
R_{thJC}	Thermal Resistance, Junction to Heatsink	0.13	$^{\circ}\text{C/W}$
M	Weight	39	g

MOSFET Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
Static characteristics (at $T_c=25^{\circ}\text{C}$ unless otherwise specified)						
BV_{DS}	Drain-source Breakdown Voltage	1200	-	-	V	$V_{GS}=0\text{V}$
I_{DSS}	Zero Gate Voltage Drain Current	-	-	100	μA	$V_{DS}=1200\text{V}; V_{GS}=0\text{V}$
I_{GSS}	Gate-body Leakage Current	-	-	500	nA	$V_{GS}=-10/20\text{V}; V_{DS}=0\text{V}$
$V_{GS(th)}$	Gate Threshold Voltage	2	-	4	V	$V_{DS}=V_{GS}; I_D=10\text{mA}$
$R_{DS(on)}$	Static Drain-source on Resistance	-	16	22	m Ω	$V_{GS}=18\text{V}; I_D=50\text{A}; T_{vj}=25^{\circ}\text{C}$
$V_{GS(on)}$	Recommended Turn-on Voltage	-	18	-	V	Static
$V_{GS(off)}$	Recommended Turn-off Voltage	-	-5	-	V	
R_G	Gate Resistance	-	2.2	-	Ω	$V_{GS}=0\text{V}; f=1\text{MHz}$
Dynamic characteristics (at $T_c=25^{\circ}\text{C}$ unless otherwise specified)						
C_{iss}	Input Capacitance	-	6878	-	pF	$V_{DS}=1000\text{V}; f=1\text{MHz}; V_{AC}=25\text{mV}$
C_{oss}	Output Capacitance	-	288	-		
C_{rss}	Reverse Transfer Capacitance	-	13	-		
E_{on}	Turn-on Energy	-	2.6	-	mJ	$V_{DD}=800\text{V}; V_{GS}=-5/+18\text{V}; I_D=50\text{A};$ $\text{Load}=100\mu\text{H}; R_{G(ext)}=5\Omega$
E_{off}	Turn-off Energy	-	0.8	-		
Q_{GS}	Gate-source Charge	-	77	-	nC	$V_{DD}=800\text{V}; V_{GS}=-5/+18\text{V}; I_D=50\text{A}$
Q_{GD}	Gate-drain Charge	-	78.5	-		
Q_G	Total Gate Charge	-	239	-		
$t_{d(on)}$	Turn-on Delay Time	-	52	-	ns	$V_{DD}=800\text{V}; V_{GS}=-5/+18\text{V}; I_D=50\text{A};$ $R_{G(ext)}=5\Omega; \text{Load}=100\mu\text{H}$
t_r	Rise Time	-	39	-		
$t_{d(off)}$	Turn-off Delay Time	-	83	-		
t_f	Fall Time	-	19	-		

Body Diode Characteristics (at T_J=25°C unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
V _{FSD}	Forward Voltage	-	-	6	V	V _{GS} =0V; I _F =50A
I _S	Continuous Diode Forward Current	-	50	-	A	V _{GS} =0V; T _C =25°C
t _{RR}	Reverse Recovery Time	-	98	-	ns	V _{GS} =-5/+18V; I _F =50A; V _R =800V
Q _{RR}	Reverse Recovery Charge	-	615	-	nC	
I _{RRM}	Peak Reverse Recovery Current	-	18	-	A	

NTC Thermistor Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
R ₂₅	Rated Resistance	-	5.00	-	kΩ	T _{NTC} =25°C
ΔR/R	Deviation of R ₁₀₀	-5	-	5	%	T _{NTC} =100°C; R ₁₀₀ =493.3Ω
B _{25/50}	Beta Value for 25°C to 50°C	-	3375	-	K	$R_2=R_{25} \exp[B_{25/50}(1/T_2 - 1/(298.15K))]$
B _{25/80}	Beta Value for 25°C to 80°C	-	3414	-	K	$R_2=R_{25} \exp[B_{25/80}(1/T_2 - 1/(298.15K))]$
B _{25/100}	Beta Value for 25°C to 100°C	-	3436	-	K	$R_2=R_{25} \exp[B_{25/100}(1/T_2 - 1/(298.15K))]$

Typical Performance

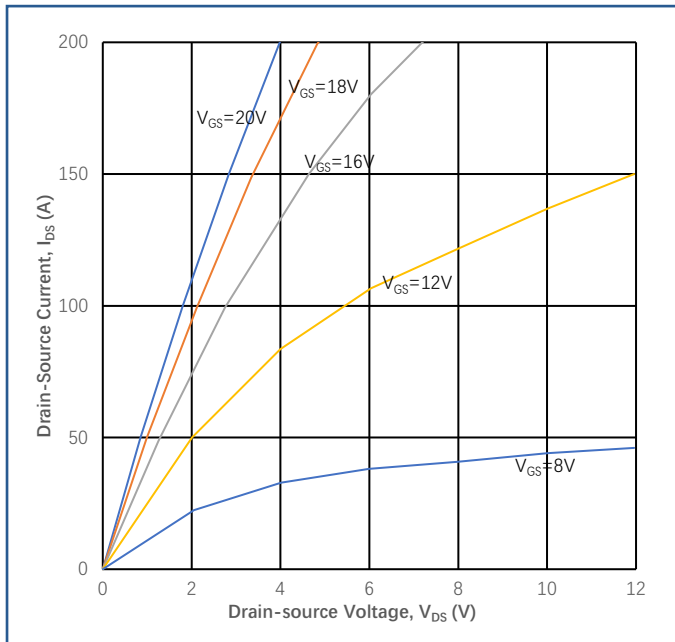


Figure 1
Output Characteristics ($T_J = 25^\circ\text{C}$)

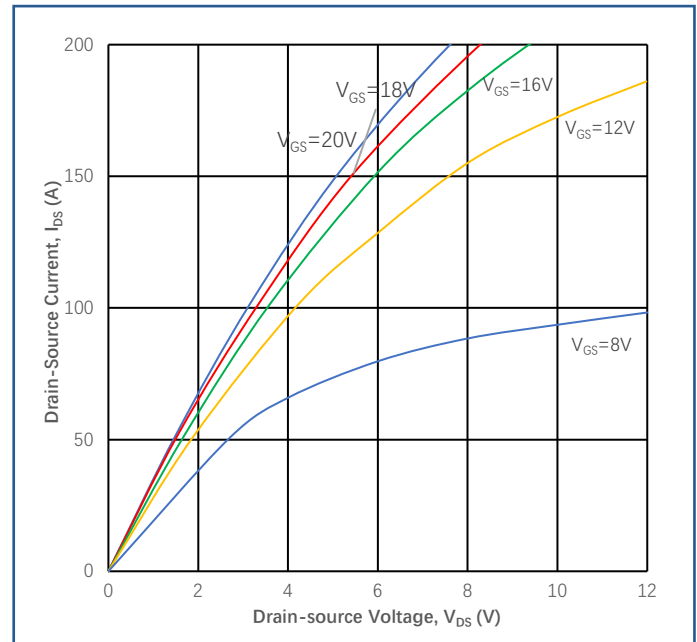


Figure 2
Typical Output Characteristics ($T_J = 150^\circ\text{C}$)

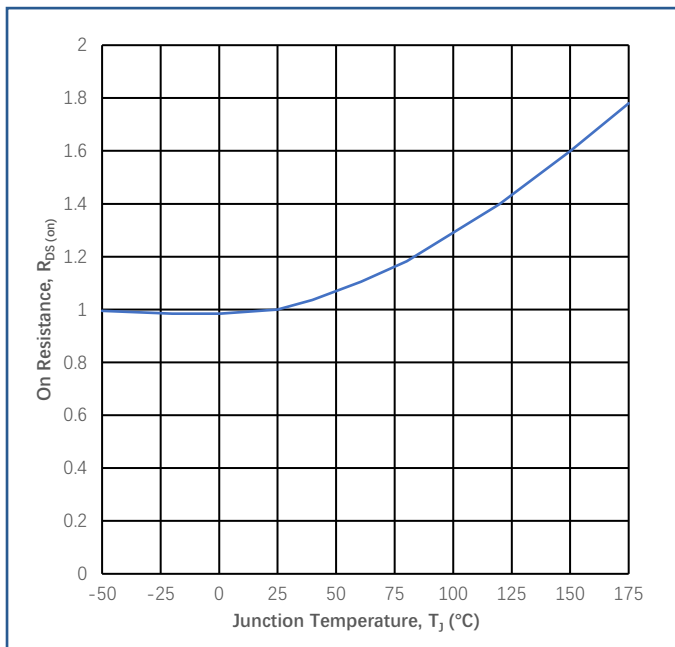


Figure 3
Normalized on-resistance vs. T_J

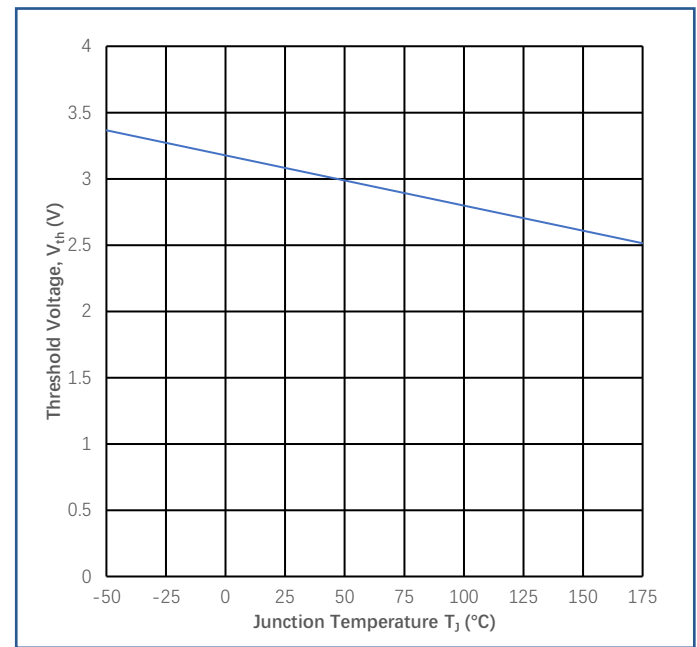


Figure 4
Threshold Voltage vs. Temperature

Typical Performance

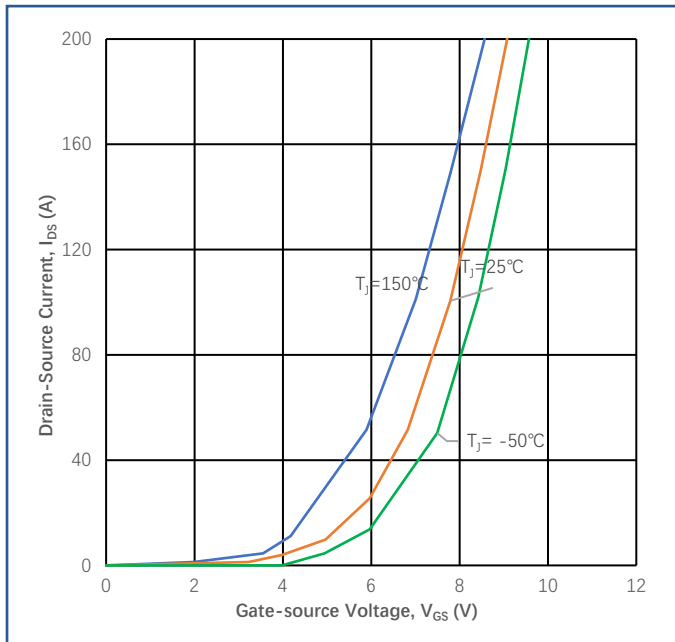


Figure 5

Transfer Characteristic for Various T_j

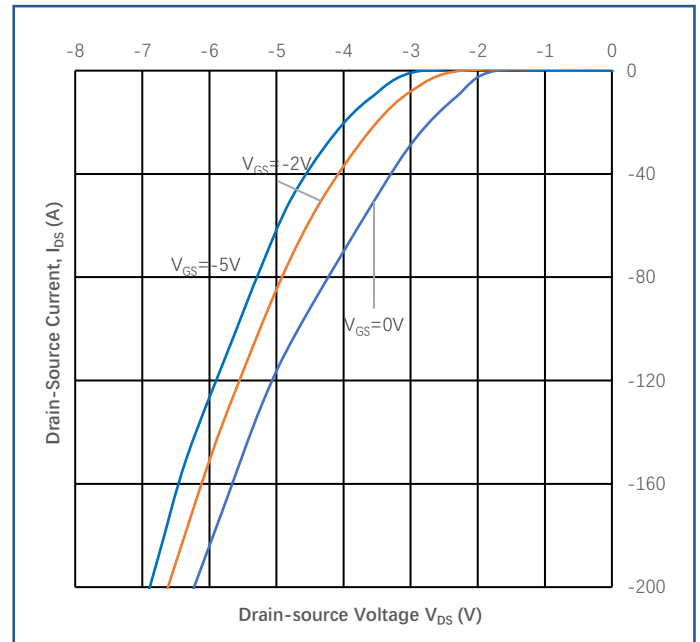


Figure 6

Body Diode Characteristic

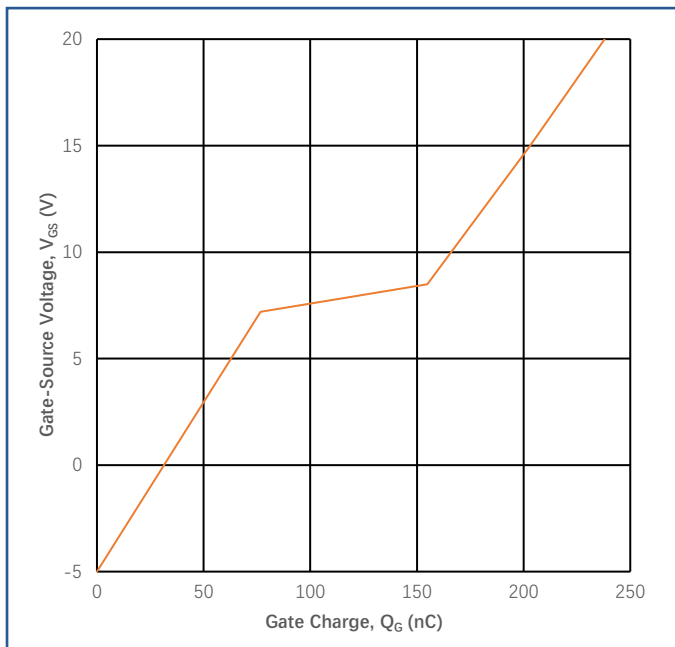


Figure 7

Gate Charge Characteristics

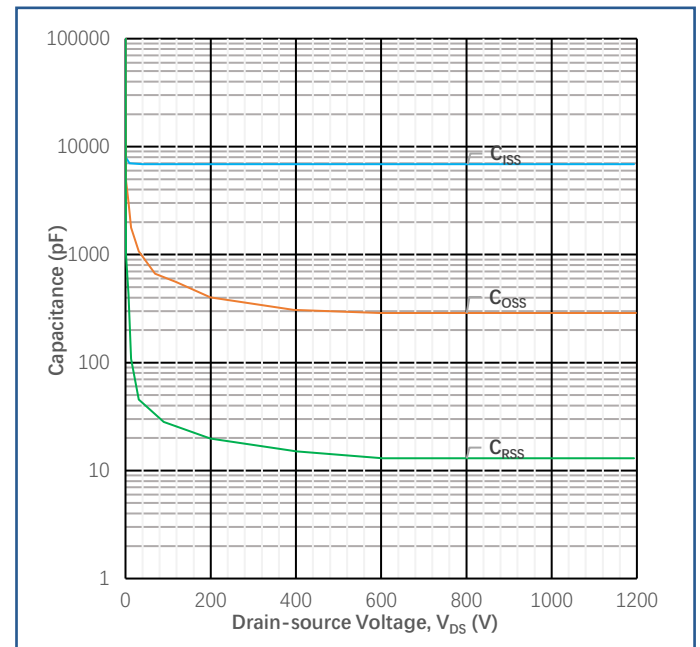


Figure 8

Capacitances vs. V_{DS}

Typical Performance

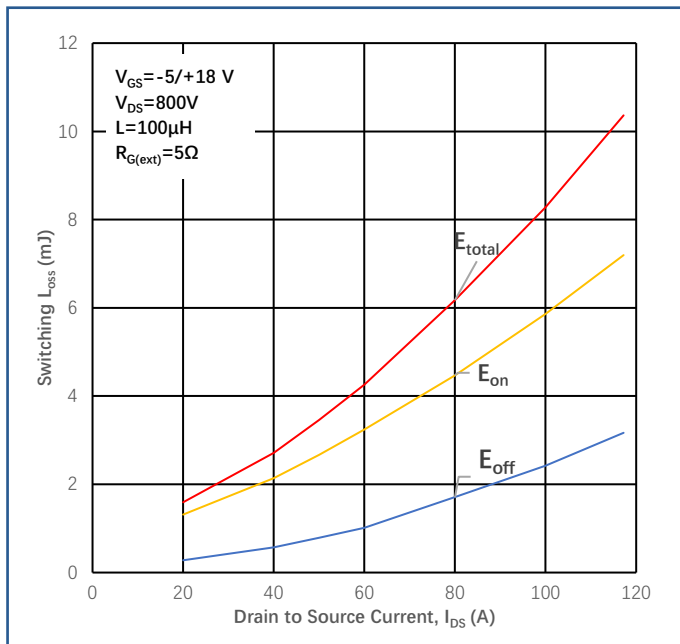


Figure 9

Inductive Switching Energy vs. Drain Current

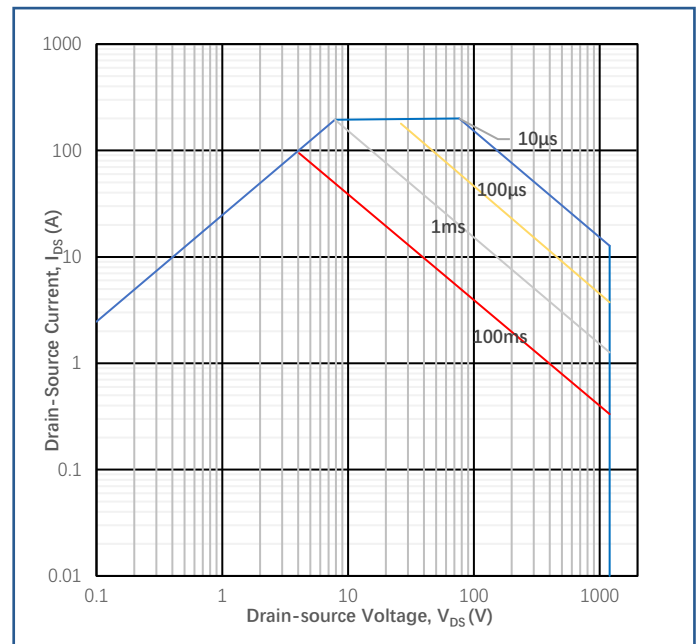
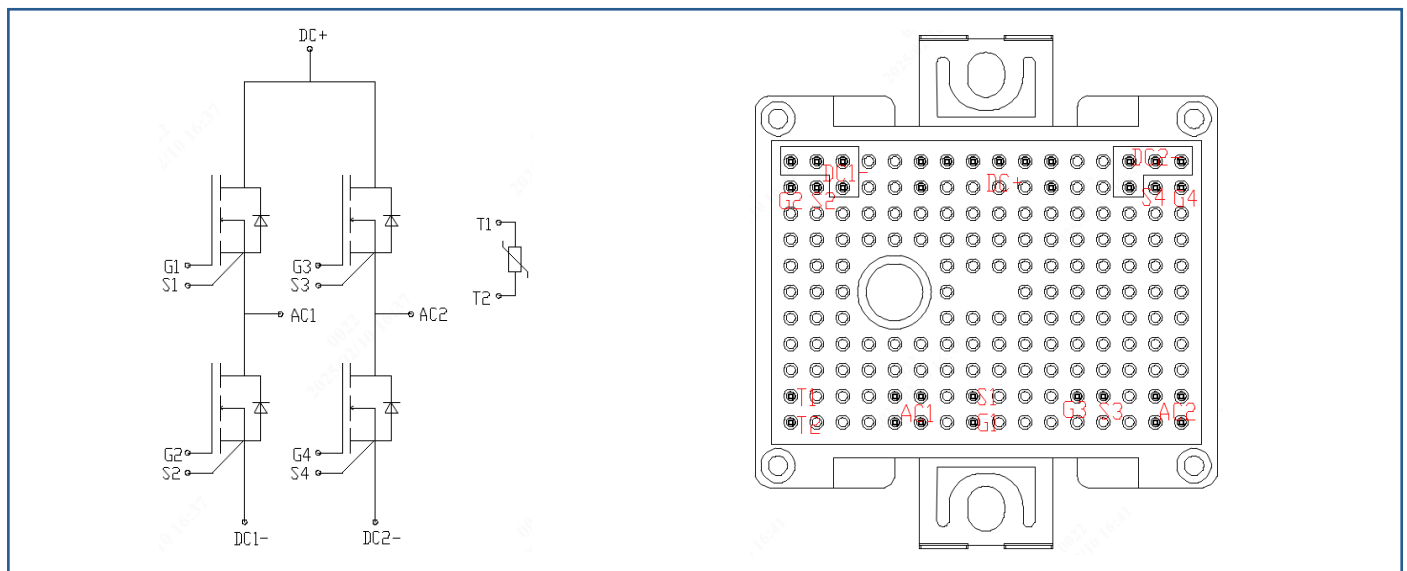


Figure 10

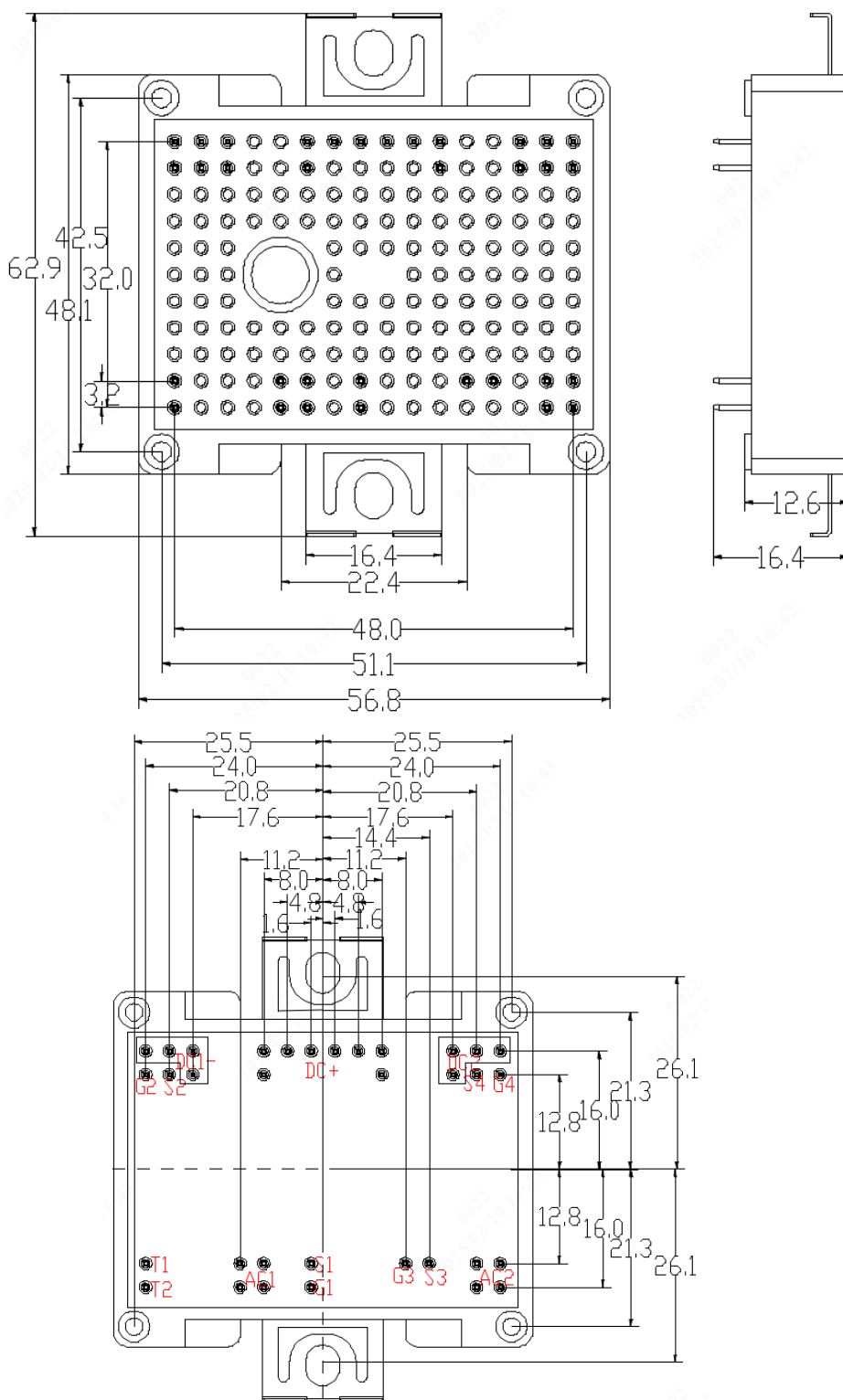
Safe Operating Area

Circuit Diagram Headline



Package Dimensions (mm)

Package Type: MEP



未标注线性公差按 GB/1804-2000c 级执行	公差分段	0.5-3	3-6	6-30	30-120	120-400
	c 级	±0.2	±0.3	±0.5	±0.8	±1.2

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